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(54) Title: IMPROVED THERMOELECTRIC MODULE WITH Si/SiC AND B₄C/B₆C SUPER-LATTICE LEGS

(57) Abstract: A super-lattice thermoelectric device. The device is comprised of p-legs and n-legs, each leg being comprised of a large number of very thin alternating layers of two materials with differing electron band gaps. The n-legs in the device are comprised of alternating layers of Si and SiC. The p-legs are comprised of alternating layers of B₄C and B₆C. In preferred embodiments the layers are about 100 angstroms thick. Thermoelectric modules made according to the present invention are useful for both cooling applications as well as electric power generation. This preferred embodiment is a thermoelectric 10 X 10 egg crate type module about 6 cm X 6cm X 0.76 cm designed to produce 70 Watts with a temperature difference of 300 degrees C with a module efficiency of about 30 percent. The module has 98 active thermoelectric legs, with each leg having more than 3 million super-lattice layers.

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IMPROVED THERMOELECTRIC MODULE WITH Si/SiC AND B₄C/B₉C SUPER-LATTICE LEGS

This invention was made in the course of contracts with the United States government and the government has rights in the invention. The present invention relates to thermoelectric devices and in particular to very thin lattice thermoelectric devices

BACKGROUND OF THE INVENTION

Workers in the thermoelectric industry have been attempting too improve performance of thermoelectric devices for the past 20-30 years with not much success. Most of the effort has been directed to reducing the lattice thermal conductivity (K) without adversely affecting the electrical conductivity. Experiments with superlattice quantum well materials have been underway for several years. These materials were discussed in an paper by Gottfried H. Dohler which was published in the November 1983 issue of Scientific American. This article presents an excellent discussion of the theory of enhanced electric conduction in super-lattices. These super-lattices contain alternating conducting and barrier layers and create quantum wells that improve electrical conductivity. These superlattice quantum well materials are crystals grown by depositing semiconductors in layers whose thicknesses is in the range of a few to up to about 100 angstroms. Thus, each layer is only a few atoms thick. (These quantum well materials are also discussed in articles by Hicks, et al and Harman published in Proceedings of 1992 1st National Thermoelectric Cooler Conference Center for Night Vision & Electro Optics, U.S.Army, Fort Belvoir, Virginia. The articles project theoretically very high ZT values as the layers are made progressively thinner.) The idea being that these materials might provide very great increases in electric conductivity without adversely affecting Seebeck

coefficient or the thermal conductivity. Harmon of Lincoln Labs, operated by MIT has claimed to have produced a superlattice of layers of (Bi,Sb) and Pb(Te,Se). He claims that his preliminary measurements suggest ZTs of 3 to 4. FIG. 1 shows theoretical calculated values (Sun et al – 1998) of ZT plotted as a function of quantum well width.

The present inventors have actually demonstrated that high ZT values can definitely be achieved with Si/Si_{0.8}Ge_{0.2} super-lattice quantum well. (See, for example, US Patent No. 5,550,387.) Most of the efforts to date with super-lattices have involved alloys that are known to be good thermoelectric materials for cooling, many of which are difficult to manufacture as super-lattices. The present inventors have had issued to them United States patents in 1995 and 1996 which disclose such materials and explain how to make them. These patents (which are hereby incorporated by reference herein) are US Patent Nos.: 5,436,467, 5,550,387. FIGS. 1A and 1B herein were FIGS. 3 and 5 of the '467 patent. A large number of very thin layers (in the '467 patent, about 250,000 layers) together produce a thermoelectric leg 10 about 0.254 cm thick. In the embodiment shown in the figures all the legs are connected electrically in series and otherwise are insulated from each other in an egg-crate type thermoelectric element as shown in FIG. 1A. As shown in FIG. 1B current flows from the cold side to the hot side through P legs and from the hot side to the cold side through N legs. (Electrons flow in the opposite direction.) These patents disclose super-lattice layers comprised of: (1) SiGe as conducting layer and Si as a barrier layer and (2) alternating layers of two different alloys of boron carbide. In the '387 patent Applicants disclose that they had discovered that strain in the layers can have very beneficial effects on thermoelectric properties of the elements disclosed in the '467 patent.

What are needed are better quantum well materials, even better than the ones discussed above, for thermoelectric devices.

SUMMARY OF THE INVENTION

The present invention provides a super-lattice thermoelectric device. The device is comprised of p-legs and n-legs, each leg being comprised of a large number of alternating layers of two materials with differing electron band gaps. The n-legs in the device are comprised of alternating layers of Si and SiC. The p-legs are comprised of alternating layers of B₄C and B₉C. In preferred embodiments the layers are about 100 angstroms thick. Thermoelectric modules made according to the present invention are useful for both cooling applications as well as electric power generation. This preferred embodiment is a thermoelectric 10 X 10 egg crate type module about 6 cm X 6cm X 0.76 cm designed to produce 70 Watts with a temperature difference of 300 degrees C with a module efficiency of about 30 percent. The module has 98 active thermoelectric legs, with each leg having more than 3 million super-lattice layers.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A and 1B, and 2A and 2B are cross-sections of films of thermoelectric layers.

FIG. 3 shows a cross section of a stack of films of thermoelectric layers.

FIG. 4A is a top view and FIG. 4B is a side view of the stack of films of thermoelectric layers.

FIG. 5 shows a thermoelectric leg cut from the stack of films of thermoelectric layers.

FIG. 6 shows an egg crate for holding 100 of the thermoelectric legs to form a thermoelectric module.

FIG. 7 shows the path of current through the legs of the thermoelectric module.

FIG. 8 shows a preferred technique for producing the films of thermoelectric layers.

FIG. 9 shows a test set-up.

FIG. 10 shows test results.

FIG. 11 shows thermoelectric progress over the past 54 years.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

Applicants Earlier Patents

On August 1, 2000 Applicants were granted US Patents 6,096,964 and 6,096,965 both of which have been incorporated herein by reference. In these patents Applicants disclose techniques for placing the thin alternating layers on film substrates. In these patents the alternating layers specifically described include layers comprised of silicon and silicon-germanium. The silicon is referred to as barrier layers and the SiGe layers are referred to as conducting layers and are appropriately doped to produce n legs and p legs.

An n-doping atom is typically the atom having one more electron than the base semiconductor atoms. The extra atom provides a conducting electron supporting current flow. A p-doping atom is typically the atom having one fewer electron than the base semiconductor atoms. The missing electron becomes an electron acceptor location (i.e., a hole) supporting current flow. As explained in the Dohler article, in these very thin layers electrons made available for conduction in the n-doped conduction layer can migrate to the boundary layer to make conduction possible there. Applicants believed that the excellent conducting properties of these materials are due to the fact that conduction can take place through the boundary layer crystals without being impeded by ions in the crystals which produce electrostatic fields which impede the flow of electrons. The same reasoning applies to the p-doped layers. In this case excess electrons migrate from the boundary layers to the p-doped conduction layers to produce holes in the boundary layers without current impeding ions. Thus, resistance to current flow is enormously reduced. Some materials possess thermoelectric properties without doping. In the '387 patent Applicants disclose that the layers of boron-carbide would make very good thermoelectric material especially for the p-type legs. GeTe and PbTe were also proposed as possible materials for the T/E elements.

Although the SiGe/Si superlattice material performs very well at low and moderate temperatures, performance above about 250 C is not much better than bulk SiGe alloys. Applicants' boron carbide quantum wells perform very well at low temperature and high temperatures as p-legs and but do not perform well as n-legs. It is for this reason that Applicants investigated and subsequently discovered the very good thermoelectric properties of Si/SiC material. A preferred embodiment of the present invention provides p-legs and n-legs that perform very well at high temperatures with an expectation that thermoelectric modules using these two legs will have module efficiencies of about 30% to 40%.

Applicants' Experiments

Applicants have produced a test quantum well thermoelectric couple with 11 microns of thermoelectric layers on a 5-micron silicon film that has operated at 14 percent conversion efficiency. This efficiency was calculated by dividing the power out of the couple by the power in to an electric heater with no correction for extraneous heat losses. The accuracy of the experimental set-up used was validated by measurement of the 5 percent efficiency of a couple fabricated of bulk Bi_2Te_3 alloys. The test set-up is shown in FIG. 9 and the results are shown in FIG. 10.

Figure of Merit

The thermodynamic efficiency, η , for a thermoelectric power generator is given by:

$$\eta = \{(T_h - T_c)/T_h\} \{(M - 1)/(M + T_c/T_h)\}$$

where M is defined by

$$M = \{1 + Z(T_c + T_h)/2\}$$

For a specific thermoelectric material, the figure of merit, Z, must be high:

$$Z = \sigma \alpha^2 / \kappa_L \kappa_e$$

where σ is the electrical conductivity, α is the Seebeck coefficient, κ_L is the lattice or phonon contribution to the thermal conductivity and κ_e is the electron

contribution to the thermal conductivity. For good efficiency Z must be high. Much effort has been expended to increase the figure without much success until the past few years as indicated in FIG.11 that shows ZT improvements. Applicants' discoveries have been important in bringing about these improvements as indicated in FIG. 11 and also in Applicant's patents cited in the Background section. In 2002 Applicants demonstrated ZT values of about 4.0 and measured actual efficiencies of about 14 percent with Si/SiGe n-legs and B_4C/B_9C p-legs. Each leg was only 11 microns thick on a 5 micron Si substrate.

Si/SiC

Recent test results by Applicants indicate that Si/SiC multi-layer films exhibit very favorable Seebeck coefficient (α), resistivity (ρ) (see Table I) and power factor (α^2/ρ) values as shown in Table I. If their thermal conductivity values are low over the full operating temperature range, as expected for quantum well materials, the thermoelectric figure-of-merit should be close to that of B_4C/B_9C . Further, the power factor values are expected to increase with increasing temperature due to a decrease in resistivity and an increase in Seebeck coefficient. Si/SiC multi-layer films are therefore highly promising for n-leg application, offering prospects of both a high thermoelectric figure-of-merit and a high operating temperature, based on the refractory nature of silicon carbide. The Applicants are convinced that B_4C/B_9C - Si/SiC QW couples will exhibit module efficiencies much improved over prior art couples. They project module efficiencies of 30% to 40%, is a giant step in thermoelectric development.

Recent measurements at UCLA indicate that the thermal conductivity of the B_4C/B_9C multi-layer films is significantly reduced in comparison with the bulk value. The use of the UCLA low value for the in-plane thermal conductivity leads to a factor of 3 enhancement in the performance (i.e., figure of merit) of the material. The data based on the assumption of the UCLA thermal conductivity value are also included in Table 1 and Figure 5 and show the promise of this technology. Measurements at UCLA on multi-layer QW films of Si/SiGe also

showed a reduction in thermal conductivity by about a factor 3 in comparison with bulk material. The measurement to date has been made only at room temperature.

Applicants' Demonstration Projects

Applicants have successfully produced Si/SiC multi-layer quantum well films. Magnetron sputtering was used to deposit films of SiC with Si as the barrier material, on silicon substrates. Films of individual layer thickness about 100 Å, and up to 10,000 Å in total thickness, were deposited. Applicants believe that this is the first time that multi-layer films of Si/SiC have been successfully deposited. Measurements on these materials indicated excellent resistivity and Seebeck coefficient values. Table 1 shows the thermoelectric properties of these films at room and higher temperatures. These numbers confirm the promise of this material combination, resulting from QW confinement of the carriers. Based on thermal conductivity measurements of Si/SiGe and B₄C/B₉C films, which have a factor of 3-4 reduction versus bulk alloys, these multi-layer QW Si/SiC films are expected on theoretical grounds to show similar reductions in thermal conductivity. These experiments show that Si/SiC is a preferred choice for the n-leg of a highly efficient thermoelectric power conversion device.

TABLE I		
Temperature (°C)	Resistivity (mΩ-cm)	Seebeck Coefficient (μV/°C)
25	2.15	-750
250	1.71	-1080
500	1.52	-1240

Film deposition was performed using a Veeco magnetron sputtering unit at Hi-Z, with 3-inch targets, and by side-sputtering using 2 or 3 inch targets at the University of California, San Diego (UCSD). Techniques were developed to control and measure the thickness of each layer, with a typical target of 100 Å per layer, deposited in about 1 minute. Deposition normally occurred on a [100]

silicon wafer 3 inches in diameter. Some non-uniformity was noted around the edges of the wafer, so samples for measurement were taken from the central area. In the case of the B₄C/B₉C multi-layer films, annealing was performed prior to measurement.

First Preferred Embodiment

B₄C/B₉C and Si/SiC Super-lattice Module

In this first preferred embodiment thermoelectric elements are made with p-type legs comprised of super-lattices of alternating layers of B₄C and B₉C and n-type legs comprised of a super-lattices of alternating layers of Si and SiC. Both B₄C/B₉C (as a p-leg) and Si/SiC (as an n-leg) function as thermoelectric elements without added doping.

Materials and Equipment for Producing Thermoelectric Film

The following special materials and equipment are needed to produce thermoelectric film for this first preferred embodiment:

- 1) Silicon sputtering targets of approximate size of 10 X 12 inches.
- 2) Si/SiC sputtering targets of approximate size of 10 X 12 inches.
- 3) B₄C/B₉C sputtering targets of approximate size of 10 X 12 inches.
- 4) A large number of 5-micron thick p-doped and n-doped Si substrate wafers approximately 6 inches in diameter.
- 5) A sputtering machine with at least 62 inch diameter vacuum chamber, with three direct current sputtering magnetometers, and all the typical supporting instrumentation, such as vacuum pumps, power supplies, monitoring instruments, etc. These machines are available from several suppliers such as AJA International, Inc.
- 6) Substrate holders with heating elements for heating substrates to 1000 degrees C.
- 7) Measuring equipment for measuring alternating current resistivity, Seebeck coefficient, and thermal conductivity.

- 8) Cutting equipment for cutting finished film or stacks of film to desired shapes.
- 9) Tools for assembling quantum well thermoelectric modules into completed egg crate assemblies.

Fabrication of Si/SiC Quantum Well Thermoelectric Film

FIG. 8 is a drawing of the primary elements of a DC sputtering magnetometer set up to produce Si/SiC thermoelectric film. One of the 5-micron thick n-doped silicon wafers which will function as a silicon substrate 18 is placed on a graphite holder 19 as shown at 20 in FIG. 8A. One of the Silicon targets 22 is placed on high voltage target holder 24 and a SiC target 26 is placed on high voltage target holder 28. The targets are maintained at 800 volts with a current of about 0.1 amps. The sputtering chamber is brought to a vacuum of about 15 – 20 microns of Hg with a pure argon environment. Argon ions bombard the targets releasing target atoms from target 22 that collect on the substrate 18. The substrate 18 should be maintained at a temperature of about 375 degrees C to help balance out stresses that otherwise tend to develop in the deposited film. The sputtering magnetometer is operated so as to deposit 100-Angstrom (0.1 micron) layers on substrate 18 at the rate of about one layer per minute. After the first silicon layer is deposited, substrate holder is pivoted so that substrate 18 is positioned over SiC target 26 and a 100-Angstrom layer of SiC is deposited on top of the 100-Angstrom silicon layer. This process is repeated until 95 layers 100 Angstrom layers have been deposited on substrate 18. Then a 500-Angstrom layer of silicon is deposited on top of the 95 layers to produce a sequence of layers 1.0-micron thick as shown in FIG. 1A. This sequence is then repeated 29 times as shown in FIGS. 1A and 2A until 30 sequences of layers have been deposited to produce a film 6 inches in diameter with a total thickness of 0.035 mm (35 microns). The film has 2,850 thermoelectric quantum well layers each about 100 Angstroms thick. After fabrication the film preferably should be checked for thermoelectric properties including resistivity, Seebeck coefficient

and thermal conductivity. The figure of merit should be about 0.01 (1/K) or better.

Making Si/SiC Thermoelectric Legs

To produce Si/SiC legs for the thermoelectric module for this embodiment, stacks of 116 films are required. So the process described above is repeated until the required quantity of film is produced. The film is then stacked as indicated in FIGS. 3, 4A and 4B to produce a stack 4-mm thick. An adhesive such as super glue (which dissipates when heated) can be used to hold the layers together. Si/SiC thermoelectric legs with dimensions 4 mm X 4mm X 11.25 mm are then cut from this stack as shown 30 in FIG. 5 and FIG 4A. A diamond saw can be used or the legs can be cut with a laser cutter. A total of 49 Si/SiC legs are need for one 70-Watt module. The silicon substrate for the n-legs should be n-doped.

B₄C/B₉C Thermoelectric Legs

B₄C/B₉C legs for this thermoelectric module are produced with the same procedure described above except B₄C replaces the silicon as target material and as thermoelectric layers. The substrate however is silicon and the 0.05 micron silicon layer between sequences of layers is also silicon, all as shown in FIG. 1B and 2B. For these legs the third target structure of the sputtering magnetometer (not shown in FIG. 8) is utilized so that the silicon layers can be provided in addition to the B₄C and B₉C thermoelectric layers.

Module Fabrication

The 98 legs prepared as described above for this embodiment should now be loaded into thermoelectric egg crates of the type well known in the thermoelectric art. One such egg crate is shown at 38 in FIG. 6. The egg crate provides insulated slots for 100 legs. Two slots are used for copper lead connections and to provide support for the leads, these slots are preferably filled with a bulk material the same as the material in the adjacent connected slot. Preferably a very thin molybdenum layer is deposited on exposed surfaces of the legs as

shown at 40 in FIG. 7 and aluminum is sprayed as shown at 42 on both the hot and cold sides of the module to connect all of the legs in series. After spraying the aluminum is ground down to the insulating wall 44 to isolate each leg from all other legs except one leg at the module cold side and one leg at the module hot side. The direction of current flow is shown at 46 in FIG. 7.

Operation

The completed module has dimensions of about 6 cm X 6 cm X 1.4 cm and is designed to produce 70 Watts at a temperature difference of 300 degrees C. with a heat flux of 10 W/cm². The modules are useful for waste heat recovery, auxiliary power units, self-powered engine heaters, space power, and low temperature detector cooling. Applicants estimate high volume cost of these modules at \$0.20/ Watt to \$0.50/Watt compared to about \$1/Watt for conventional bulk thermoelectric modules.

SUBSTRATES

Substrates for Super-lattice Thermoelectric Material

As described in United States Patents '467, '387, '964 and '965, quantum well thermoelectric material is preferably deposited in layers on substrates. For a typical substrate as described in those patents, heat loss through the substrate can greatly reduce the efficiency of a thermoelectric device made from the material. If the substrate is removed some of the thermoelectric layers could be damaged and even if not damaged the process of removal of the substrate could significantly increase the cost of fabrication of the devices. The present invention provides a substrate that can be retained. The substrate preferably should be very thin, a low thermal and electrical conductivity with good thermal stability and strong and flexible.

Silicon

Silicon is the preferred substrate material for depositing the Si/SiC and B₄C/B₉C layers. Si has also been used by Applicants as a substrate for depositing

Si/SiGe alloys. Si is available commercially in films as thin as 5 microns from suppliers such as Virginia Semiconductor with offices in Fredericksburg, Virginia. By using a 5 micron substrate the amount of bypass heat loss can be held to a minimum. For commercial applications the quantum well film will be approximately 25 microns thick as explained above. Thus the ratio of quantum well thickness to substrate thickness is more than sufficient to greatly minimize by-pass heat losses. The silicon film is stable at much higher temperatures than Kapton.

Kapton®

Kapton is a product of DuPont Corporation. According to DuPont bulletins:

Kapton® polyimide film possesses a unique combination of properties that make it ideal for a variety of applications in many different industries. The ability of Kapton® to maintain its excellent physical, electrical, and mechanical properties over a wide temperature range has opened new design and application areas to plastic films.

Kapton® is synthesized by polymerizing an aromatic dianhydride and an aromatic diamine. It has excellent chemical resistance; there are no known organic solvents for the film. Kapton® does not melt or burn as it has the highest UL-94 flammability rating: V-0. The outstanding properties of Kapton® permit it to be used at both high and low temperature extremes where other organic polymeric materials would not be functional.

Adhesives are available for bonding Kapton® to itself and to metals, various paper types, and other films.

Kapton® polyimide film can be used in a variety of electrical and electronic insulation applications: wire and cable tapes, formed coil insulation, substrates for flexible printed circuits, motor slot liners, magnet wired

insulation, transformer and capacitor insulation, magnetic and pressure-sensitive tapes, and tubing. Many of these applications are based on the excellent balance of electrical, thermal, mechanical, physical, and chemical properties of Kapton® over a wide range of temperatures. It is this combination of useful properties at temperature extremes that makes Kapton® a unique industrial material.

Kapton® Substrate

Applicants have demonstrated that Kapton can be useful as a substrate film for super-lattice thermoelectric layers when high temperature use is not planned. Applicants have shown that a crystal layer laid down between the Kapton® substrate and the series of very thin conducting and barrier layers greatly improve thermoelectric performance especially for n-type layers. The preferred technique is to lay it on about 1000 Å thick in an amorphous form then to crystallize it by heating the substrate and the silicon layer to about 350° C to 375° C. When Kapton® is used as a substrate it can be mounted on a crystalline base that can be sand blasted off of the Kapton® after the thermoelectric film is deposited.

Other Substrates

Many other organic materials such as Mylar, polyethylene, and polyamide, polyamide-imides and polyimide compounds could be used as substrates. Other potential substrate materials are oxide films such as SiO₂, Al₂O₃ and TiO₂. Mica could also be used for substrate. As stated above, the substrate preferably should be very thin a very good thermal and electrical insulator with good thermal stability, strong and flexible.

Other Lattice Materials

Many other thermoelectric materials may be used as p-legs along with Si/SiC n-legs. Super-lattice materials are preferred. Measurements of thermal conductivity normally show a threefold reduction in QW films compared with bulk

materials, as reported below. Applicants have found that Si/SiGe multi-layer films performed well at room temperature and below, but their performance at temperatures in the range of 250 degrees C fell to that of bulk bismuth telluride.

While the above description contains many specificities, the reader should not construe these as limitations on the scope of the invention, but merely as exemplifications of preferred embodiments thereof. Those skilled in the art will envision many other possible variations within its scope. The thin layers of boron carbide and Si/SiC could be arranged in many other forms for various applications. The preferred layer thickness is about 100 Angstroms; however, layer thickness could be somewhat larger or smaller such as within the range of 200 Angstroms down to 10 Angstroms. It is not necessary that the layers be grown on film. For example, they could be grown on thicker substrates that are later removed. There are many other ways to make the connections between the legs other than the methods discussed. Accordingly, the reader is requested to determine the scope of the invention by the appended claims and their legal equivalents, and not by the examples which have been given.

We Claim:

1. A thermoelectric module comprised of:
 - A) a plurality of n-legs comprised of very thin alternating layers of silicon and silicon carbide; and
 - B) a plurality of p-legs comprised of alternating layers of boron carbide comprise two different stoichiometric forms of boron carbide;said p-legs and said n-legs being electrically connected to produce said thermoelectric module.
2. A thermoelectric module as in Claim 1 wherein said two different stoichiometric forms of boron carbide are B_4C and $B_{10}C$.
3. A thermoelectric module as in Claim 1 wherein said alternating layers are deposited on a substrate.
4. A thermoelectric module as in Claim 1 wherein said substrate is silicon.
5. A thermoelectric module as in Claim 1 wherein said substrate is silicon film.
6. A thermoelectric module as in Claim 1 wherein said substrate is a polyimide substrate.
7. A thermoelectric element as in Claim 1, wherein said polyimide substrate is Kapton®.
8. A thermoelectric element as in Claim 1, wherein said polyimide substrate is Kapton® film.
9. A thermoelectric element as in Claim 1, wherein said very thin alternating layers are about 100 Angstroms thick.
10. A thermoelectric element as in Claim 1, wherein said very thin alternating layers are each less than 200 Angstroms thick.
11. A thermoelectric element as in Claim 1 wherein said very thin alternating layers are each less than 100 Angstroms thick.
12. A thermoelectric element as in Claim 1 wherein said plurality of very thin alternating layers is about 3 million layers.
13. A thermoelectric element as in Claim 1 wherein said plurality of very thin alternating layers more than 1 million layers.

14. A thermoelectric element as in Claim 1 wherein said plurality of very thin alternating layers is at least 1250 layers.
15. A method of producing thermoelectric modules comprising the steps of:
 - A) depositing on a thin substrate a very large number of very thin alternating layers of silicon and silicon germanium to form a Si/SiC thermoelectric film;
 - B) forming a stack of said Si/SiC films produces as in step A),
 - C) producing a plurality of Si/SiC thermoelectric n-legs from said stacks of Si/SiC films,
 - D) depositing on a thin substrate a very large number of very thin alternating layers of B₄C and B₉C to form a B₄C/ B₉C thermoelectric film;
 - E) forming a stack of said B₄C/B₉C films produces as in step A),
 - F) producing a plurality of B₄C/B₉C thermoelectric p-legs from said stacks of B₄C/B₉C films,
 - G) forming a thermoelectric module from said plurality of Si/SiC thermoelectric n-legs and said plurality of B₄C/B₉C thermoelectric p-legs,
said p-legs and said n-legs being electrically connected to produce said thermoelectric module.

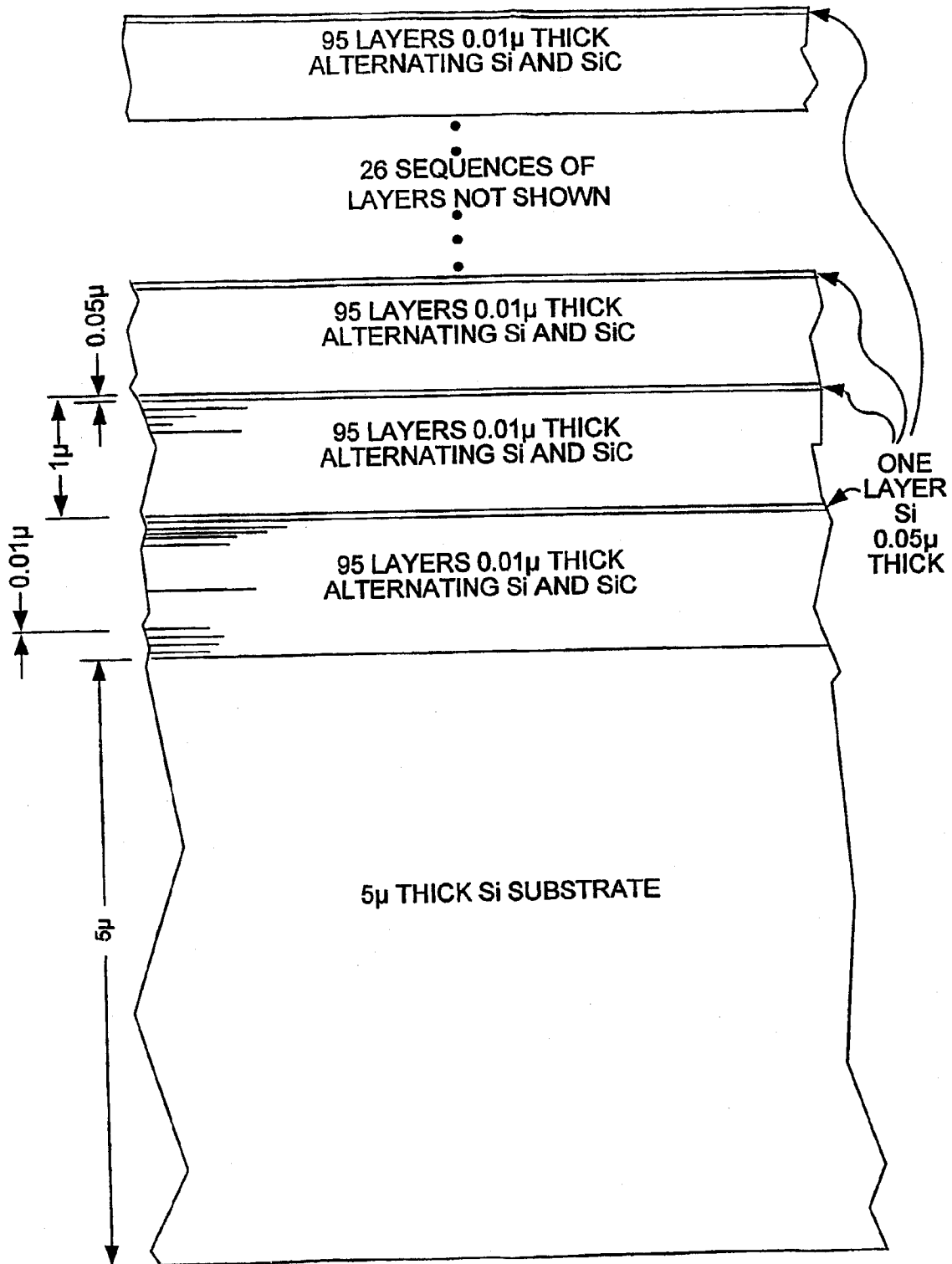


FIG. 1A

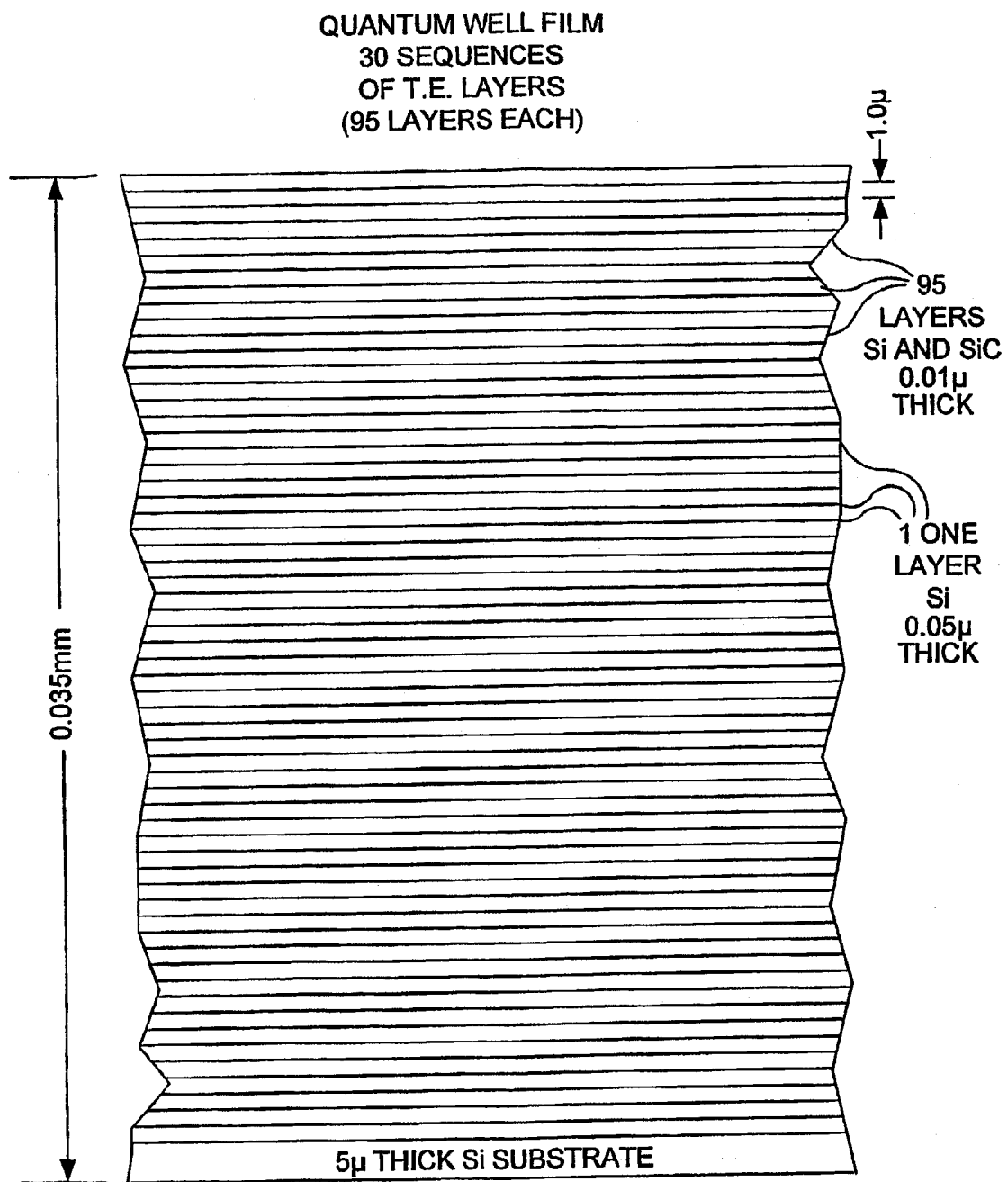


FIG. 2A

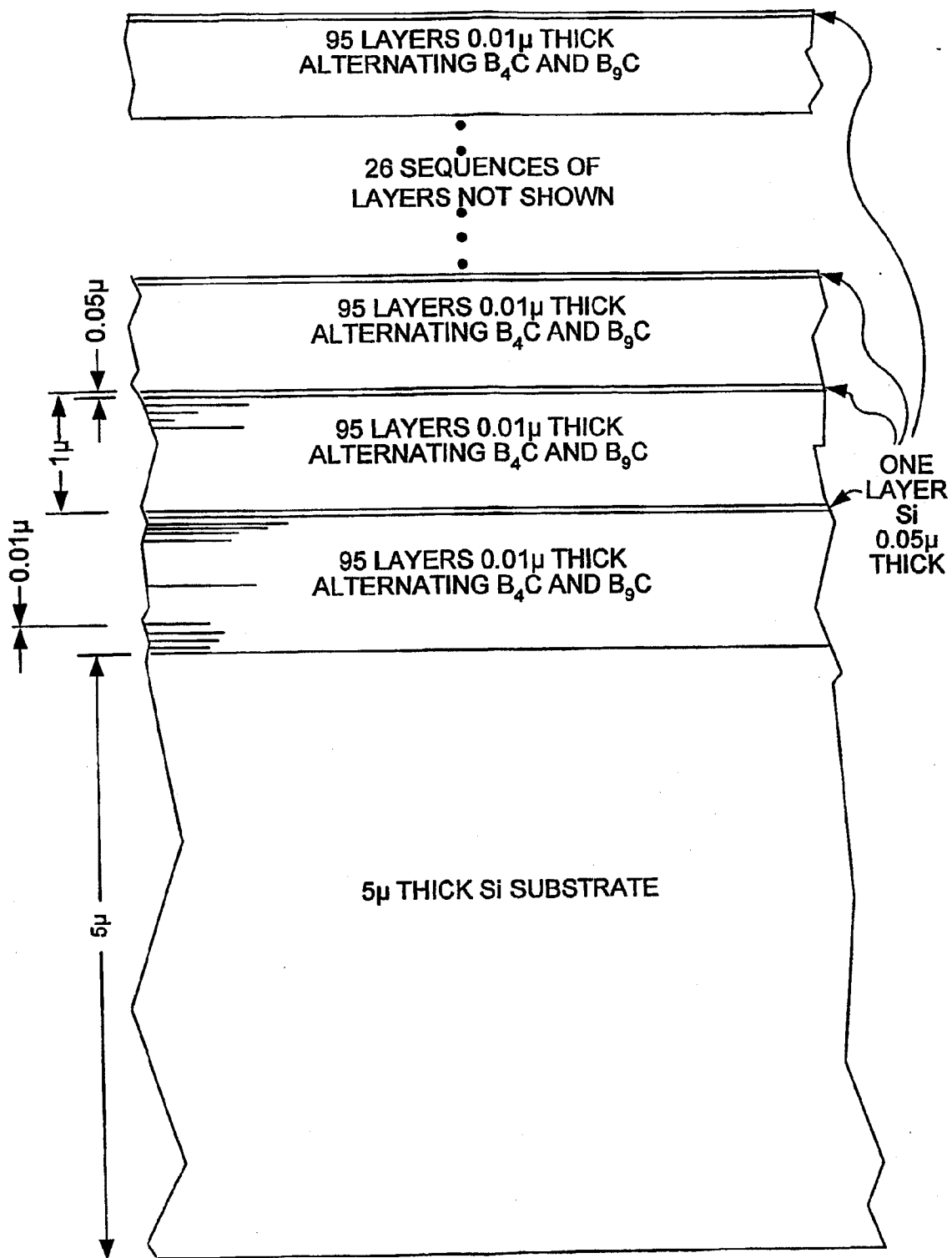


FIG. 1B

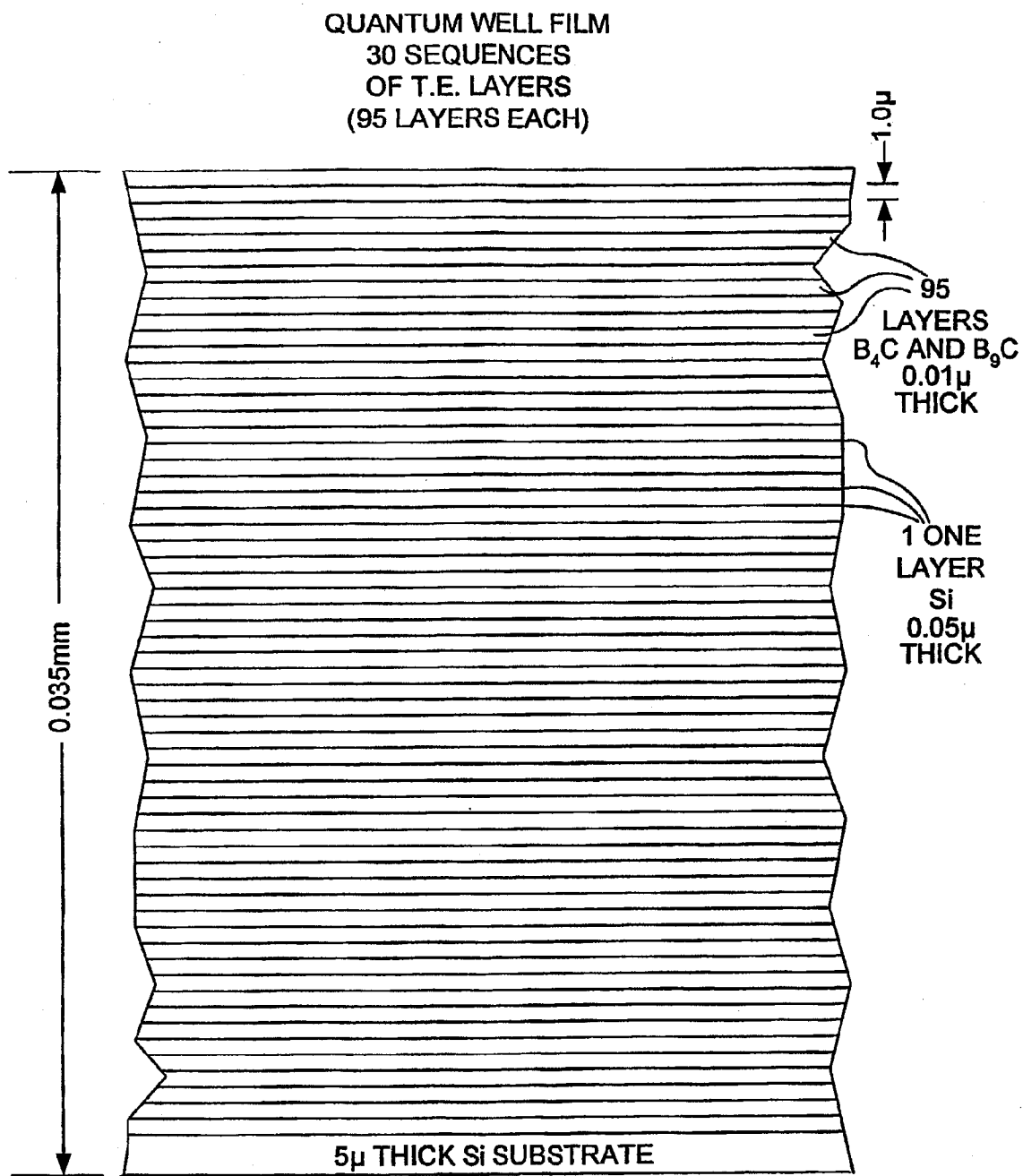


FIG. 2B

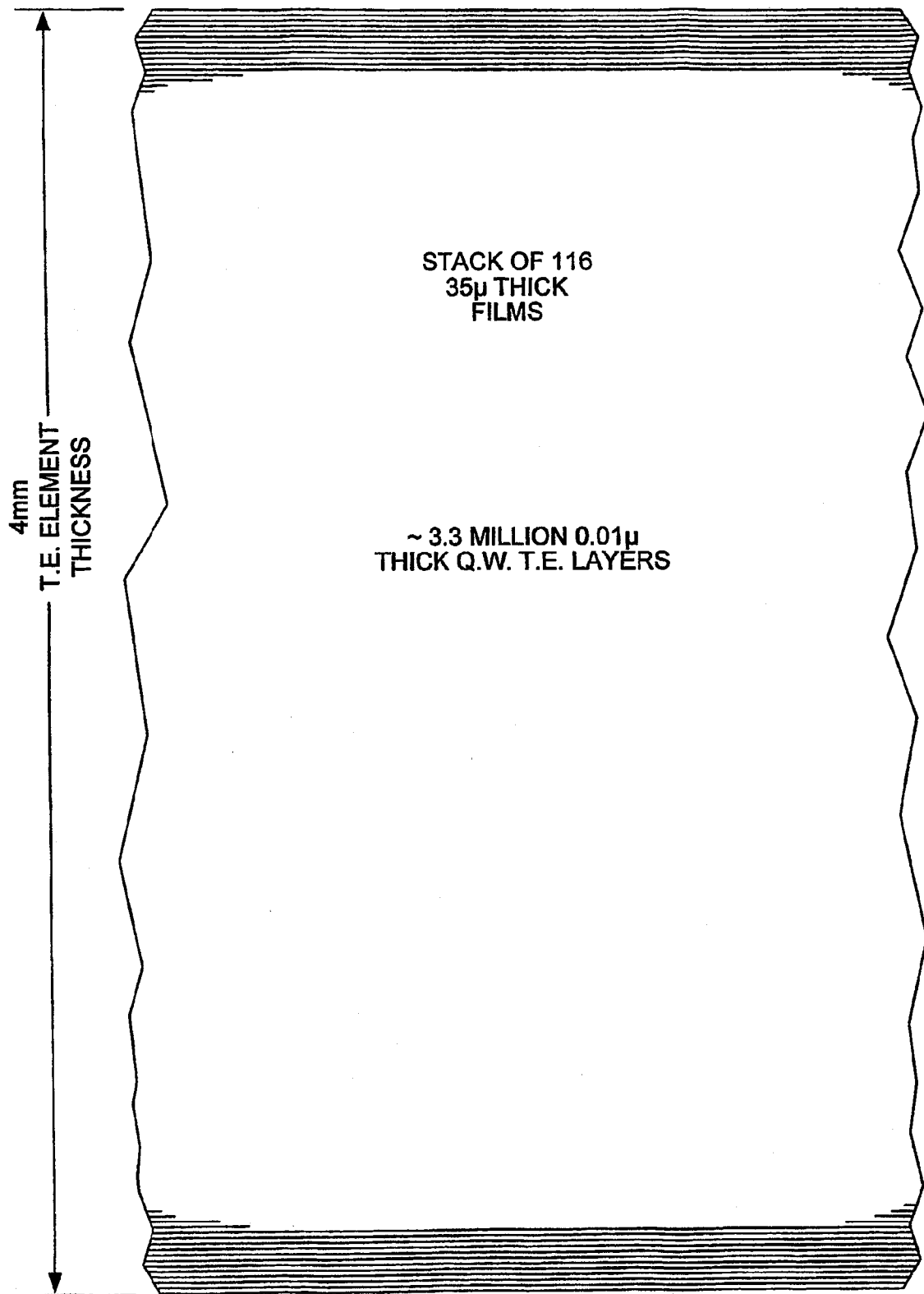
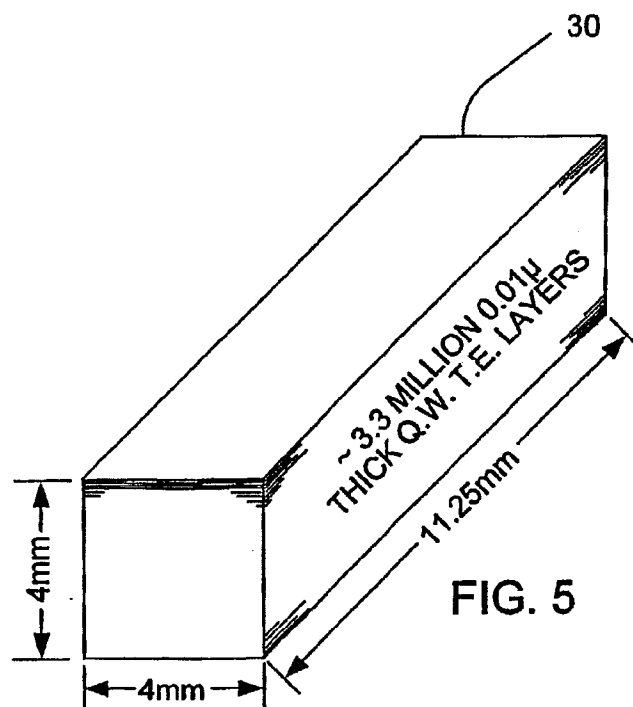
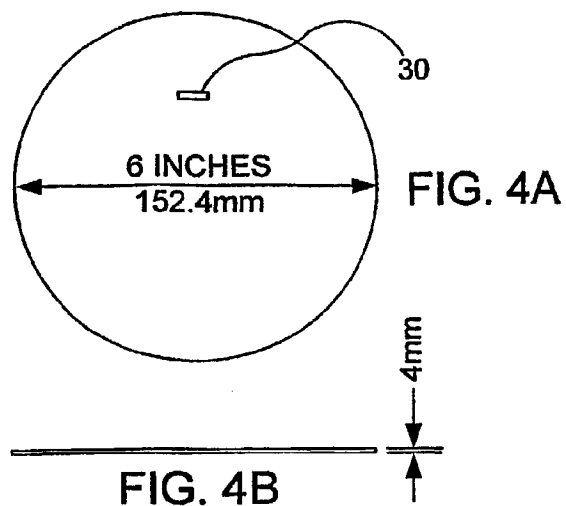


FIG. 3



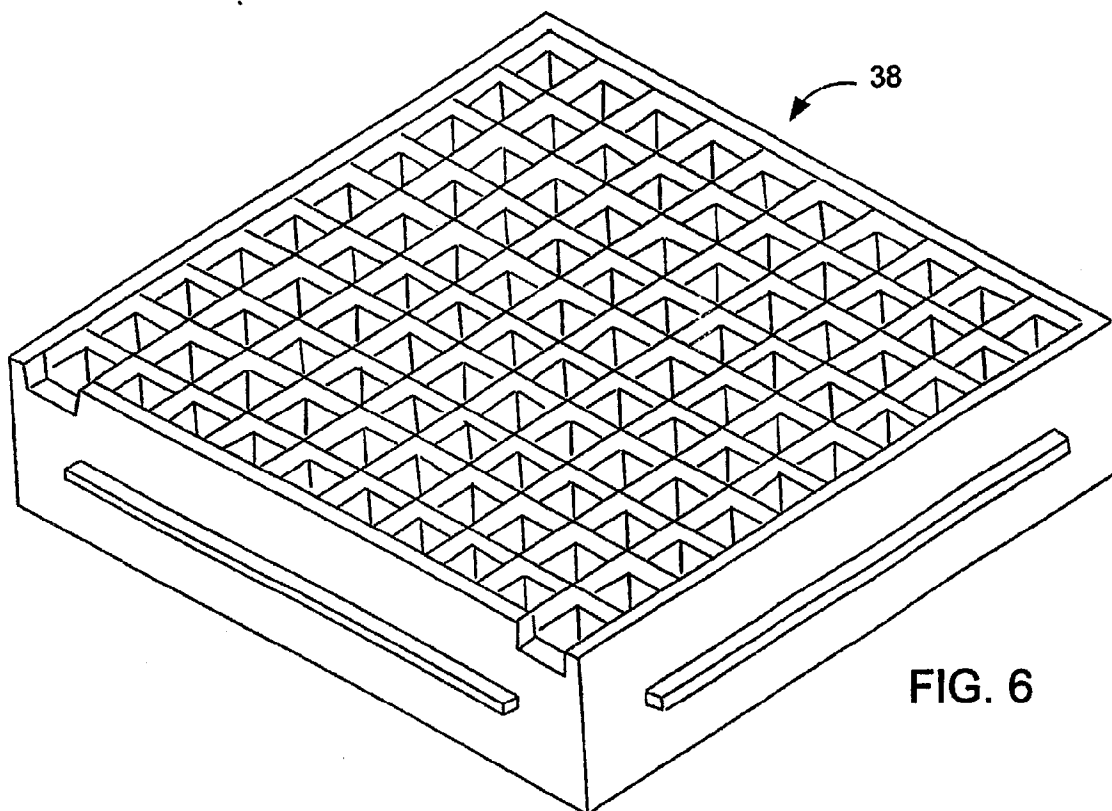


FIG. 6

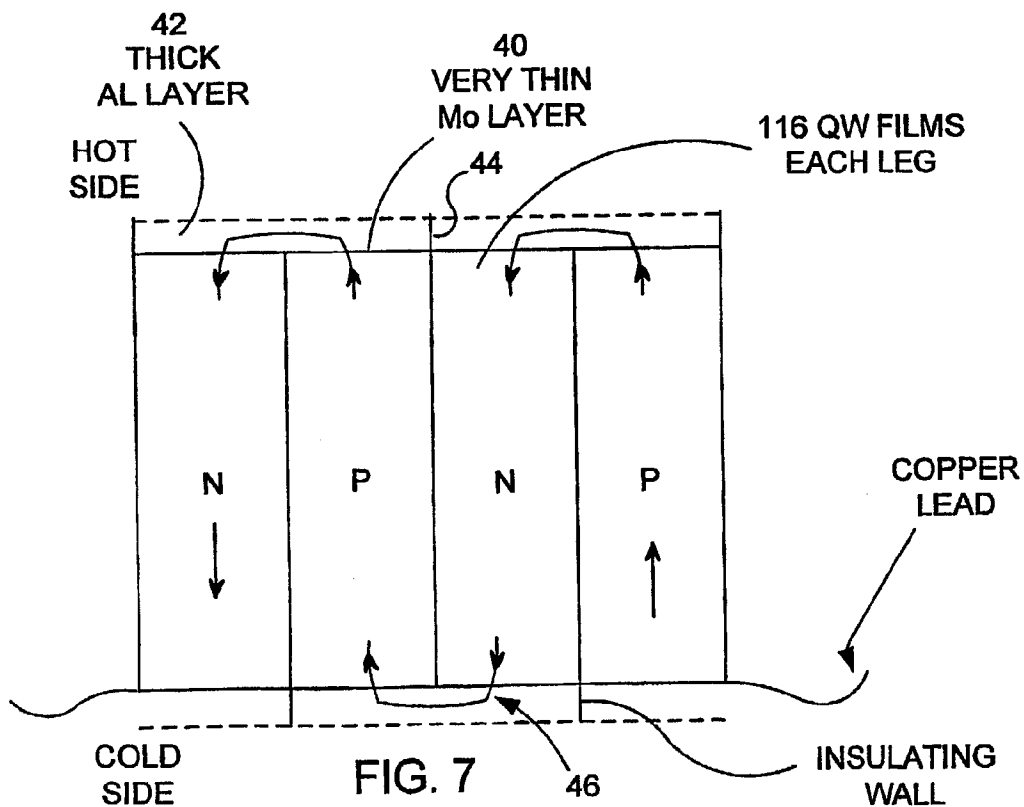


FIG. 7

DC SPUTTERING MAGNETOMETER

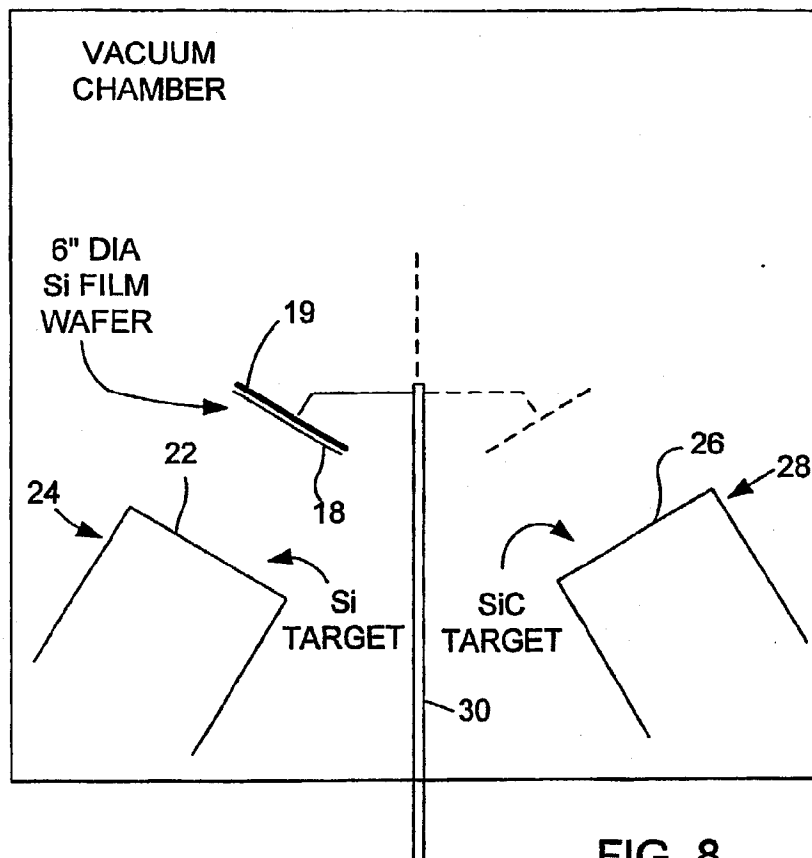


FIG. 8

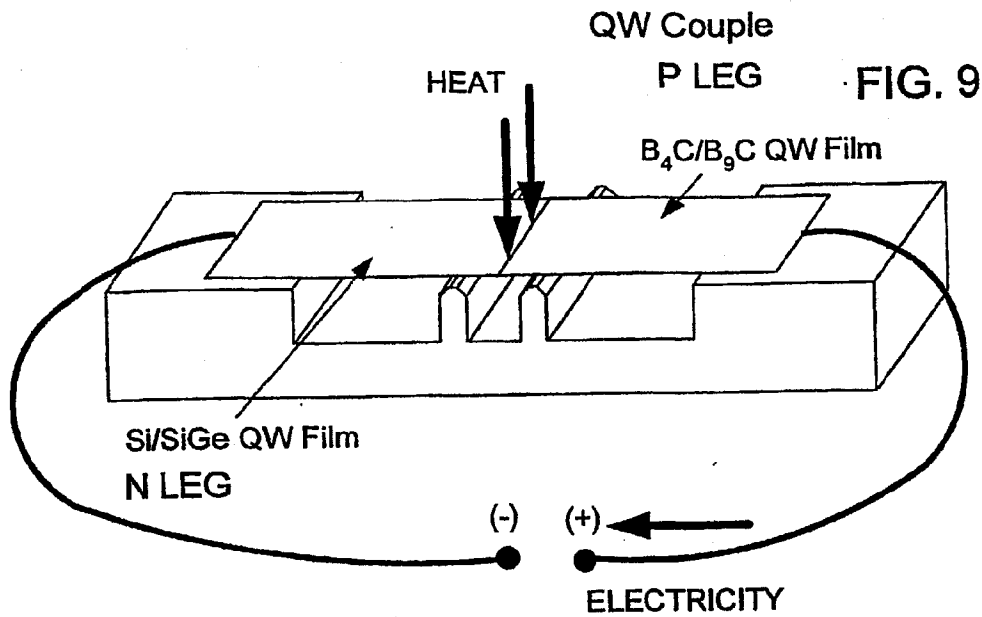


FIG. 10

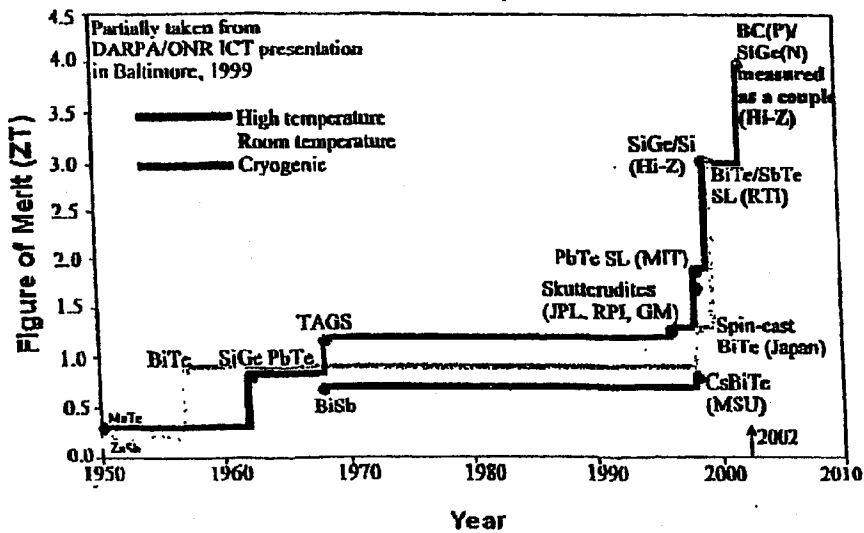
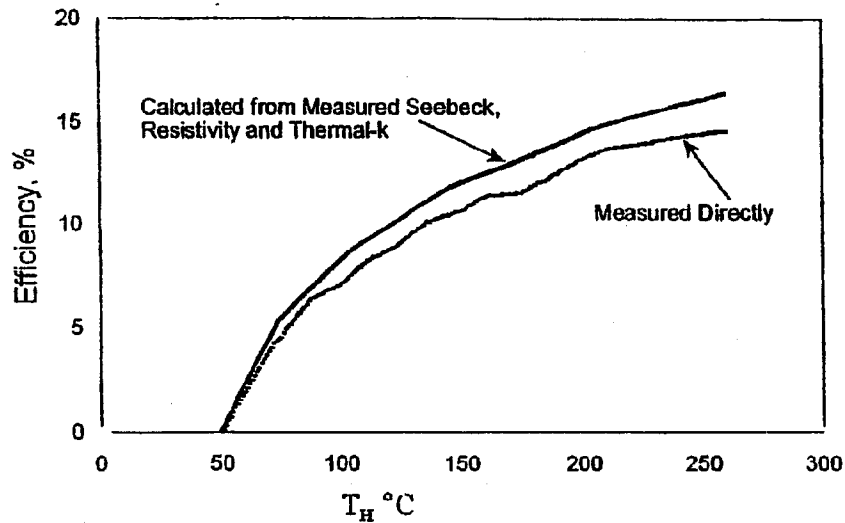


FIG. 11

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(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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(54) Title: IMPROVED THERMOELECTRIC MODULE WITH Si/SiC AND B₄C/B₉C SUPER-LATTICE LEGS

(57) Abstract: A super-lattice thermoelectric device. The device is comprised of p-legs and n-legs, each leg being comprised of a large number of very thin alternating layers of two materials with differing electron band gaps. The n-legs in the device are comprised of alternating layers of Si and SiC. The p-legs are comprised of alternating layers of B₄C and B₉C. In preferred embodiments the layers are about 100 angstroms thick. Thermoelectric modules made according to the present invention are useful for both cooling applications as well as electric power generation. This preferred embodiment is a thermoelectric 10 X 10 egg crate type module about 6 cm X 6cm X 0.76 cm designed to produce 70 Watts with a temperature difference of 300 degrees C with a module efficiency of about 30 percent. The module has 98 active thermoelectric legs, with each leg having more than 3 million super-lattice layers.

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INTERNATIONAL SEARCH REPORT

International application No.

PCT/US05/11491

A. CLASSIFICATION OF SUBJECT MATTER

IPC: H01L 35/22(2006.01),35/26(2006.01),35/34(2006.01)

USPC: 136/201,239

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
U.S. : 136/201, 239

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
Google scholar search terms: superlattice, thermoelectric, silicon carbide

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X --- Y	US 2003/0111660 A1 (GHAMATY et al) 19 June 2003 (19.06.2003), figures 2A, 3, 4A and 4C, paragraphs 0028, 0033, 0039 and 0040.	1-10, 14, 15 ----- 11-13
X,P --- Y,P	US 2004/0238022 A1 (HILLER et al) 2 December 2004 (2.12.2004), figures 2A, 3, 4A and 4C, paragraphs 0049, 0054, 0060 and 0061.	1-10, 14, 15 ----- 11-13
A	US 6,096,964 (GHAMATY et al) 1 August 2000 (1.08.2000), entire document.	1-15
A	US 6,096,965 (GHAMATY et al) 1 August 2000 (1.08.2000), entire document.	1-15

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